

PNP General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 68.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
Ic	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

 1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations. 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		PN200 PN200A	*MMBT200 *MMBT200A	
PD	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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PNP General Purpose Amplifier

(continued)

300

Electrical Characteristics	TA = 25°C unless otherwise noted
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OFF CHARACTERISTICS					

BV_{CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm B} = 0$	60		V
BV_{CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm E} = 0$	45		V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, \ I_{C} = 0$	6.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 50 \text{ V}, I_E = 0$		50	nA
I _{CES}	Collector Cutoff Current	$V_{CE} = 40 \text{ V}, I_{E} = 10$		50	nA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		50	nA

ON CHARACTERISTICS

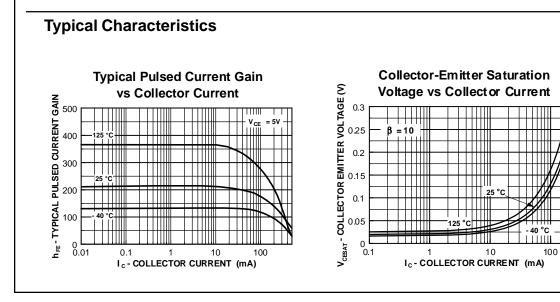
h _{FE}	DC Current Gain	$I_{C} = 100 \ \mu A, V_{CE} = 1.0 \ V$	200	80		
		$I_{C} = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	200A 200 200A	240 100 300	450 600	
		$ I_C = 100 \text{ mA}, \ V_{CE} = 1.0 \text{ V}^* \\ I_C = 150 \text{ mA}, \ V_{CE} = 5.0 \text{ V}^* $	200A 200 200	100 100 100	350	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 200 \text{ mA}, I_{B} = 20 \text{ mA}^{*}$	2007		0.2 0.4	V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 200 \text{ mA}, I_{B} = 20 \text{ mA}^{*}$			0.85 1.0	V V

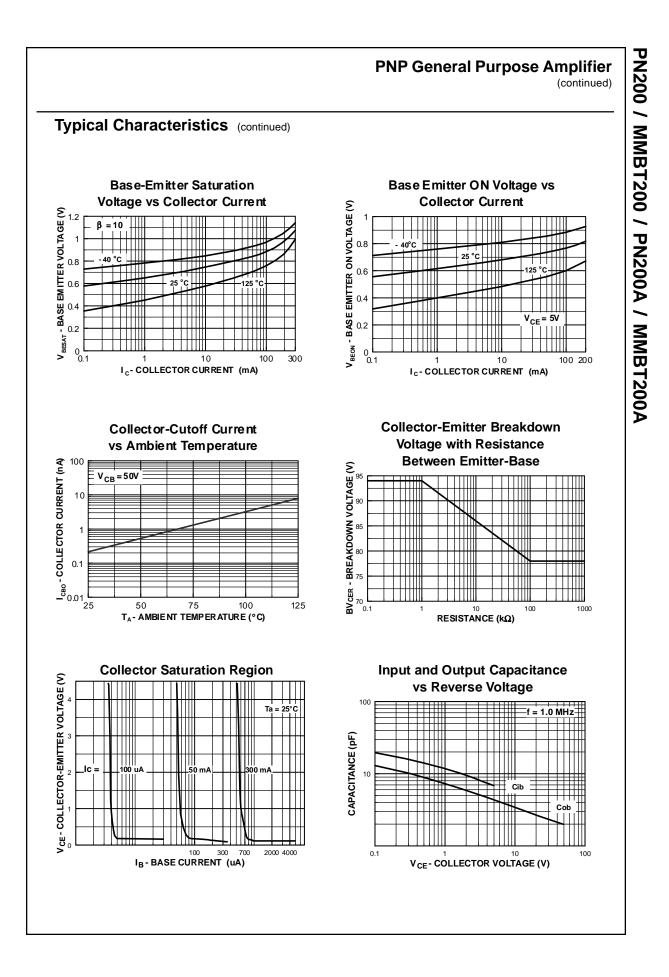
SMALL SIGNAL CHARACTERISTICS

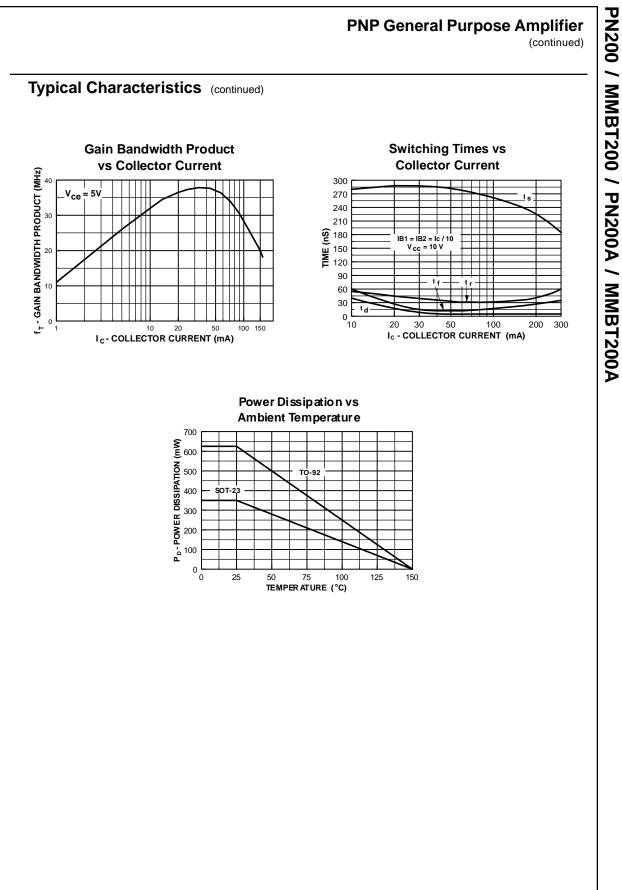
f _T	Current Gain - Bandwidth Product	$V_{CE} = 20 \text{ V}, \text{ I}_{C} = 20 \text{ mA}$	250		MHz
Cobo	Output Capacitance	V _{CB} = 10 V, f = 1.0 MHz		6.0	pF
NF	Noise Figure	$ I_C = 100 \ \mu A, \ V_{CE} = 5.0 \ V, \\ R_G = 2.0 \ k\Omega, \ f = 1.0 \ kHz $		4.0	dB dB

*Pulse Test: Pulse Width ${\leq}\,300\,\mu\text{s},$ Duty Cycle ${\leq}\,2.0\%$

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.









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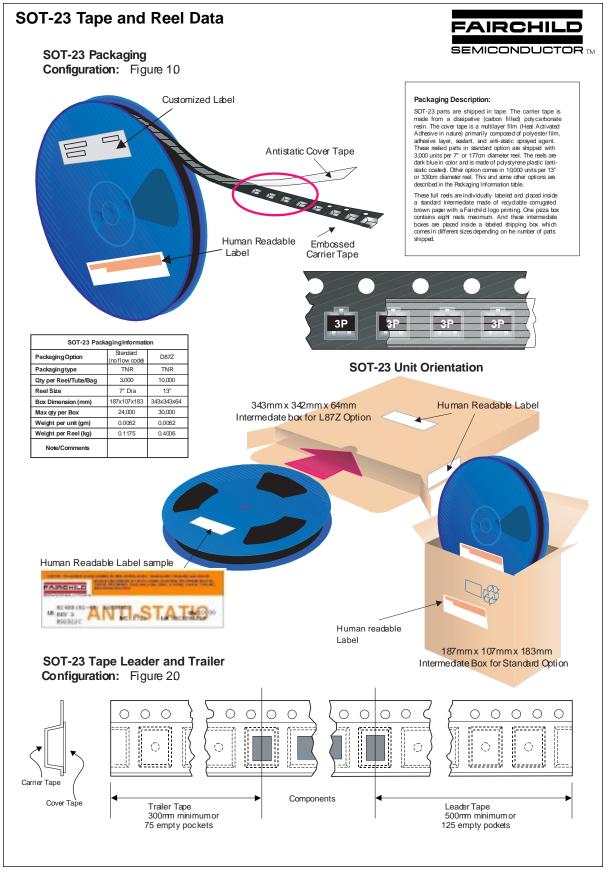
March 2001, Rev. B1





July 1999, Rev. A



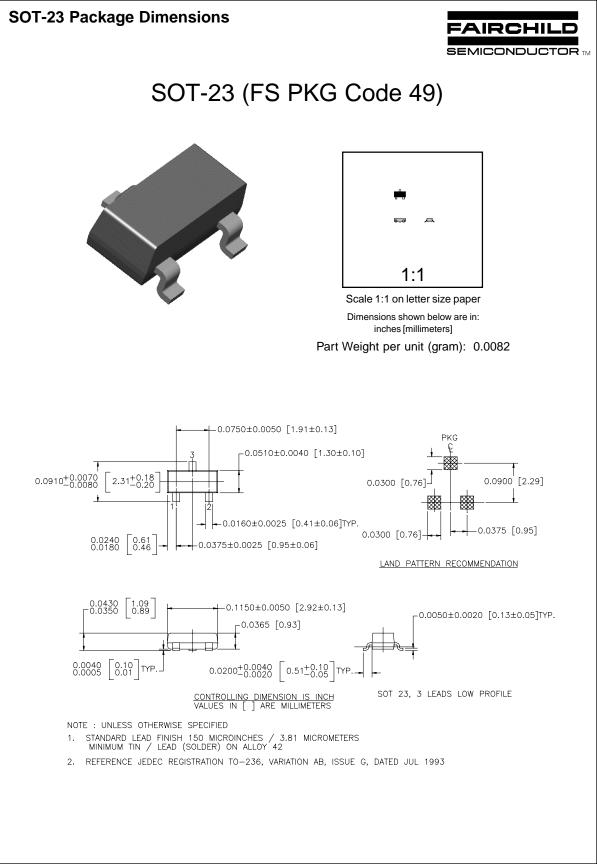


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